

## pHEMT Transistors

TriQuint Semiconductor announces ten discrete Power pHEMT transistor devices for a variety of amplifier applications including aerospace, digital radio or wireless basestations. These devices, utilizing the company's 0.35 $\mu$ m power pHEMT production process, offer impressive power, gain and efficiency performance and are suited for L- through Ku-band high power amplifiers. The TGF2021 family offers devices with gate peripheries ranging from 1 to 12 mm and is suited for high power amplifiers up to 12 W through X-band. The TGF2022 family of devices offers gate peripheries from 0.6 mm to 6.0 mm, sizes appropriate for high power amplifiers up to 8 W through Ku band. The pHEMT process allows operating drain voltages to + 12 V for increased power performance and more efficient module DC/DC conversion. Offered in die form, all devices have a protective surface passivation layer, which provides reliability and environmental robustness for both hermetic and non-hermetic applications. All devices are lead-free and RoHS compliant.

TriQuint Semiconductor

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<http://www.wirelessdesignmag.com/product-releases/2005/08/pheMT-transistors>